

# **ABSTRACT OF THE DISCLOSURE**

A test device and method for detecting alignment of word lines and deep trench capacitors in DRAM devices with vertical transistors. In the test device, an active area is disposed in the scribe line region. An H-type deep trench capacitor is disposed in the active area, and has parallel first and second portions and a third portion. Each of the first and second portions has a center and two ends. The third portion is disposed between the centers of the first and second portions. First to fourth conductive pads are disposed on the two ends of the first and second portions respectively. A bar-type conductive pad is disposed between the first and second portions, having a center aligned with a center of the third portion.